NIKO-SEM

Dual N-Channel Enhancement Mode Field Effect Transistor

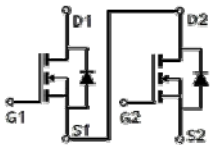
PE618DT

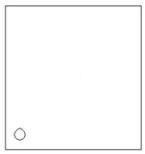
PDFN 3x3S

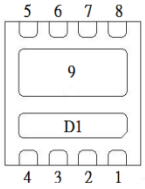
Halogen-Free & Lead-Free

PRODUCT SUMMARY

	$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
Q2	30V	7mΩ	39
Q1	30V	16mΩ	23







1 : G1
2,3,4 : D1
5,6,7 : S2
8 : G2
9 : S1/D2

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	Q2	Q1	UNITS
Drain-Source Voltage		V_{DS}	30	30	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current[3]	T_C = 25 °C	I_D	39	23	A
	T_C = 100 °C		25	14	
Pulsed Drain Current[1]		I_{DM}	50	32	
Continuous Drain Current	T_A = 25 °C	I_D	12	7.3	
	T_A = 70 °C		10	5.8	
Avalanche Current		I_{AS}	23	12	
Avalanche Energy	L = 0.1mH	E_{AS}	26	7	mJ
Power Dissipation	T_C = 25 °C	P_D	20	16	W
	T_C = 100 °C		8.3	6	
Power Dissipation	T_A = 25 °C	P_D	2.2	1.6	W
	T_A = 70 °C		1.4	1	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL		TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	$R_{\theta JA}$	Q2		56	°C / W
	$R_{\theta JA}$	Q1		77	
Junction-to-Case	$R_{\theta JC}$	Q2		6	
	$R_{\theta JC}$	Q1		7.5	

[1]Pulse width limited by maximum junction temperature $T_{J(MAX)}$=150°C.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.
[3]Package limitation current is Q2=19A , Q1=11A.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

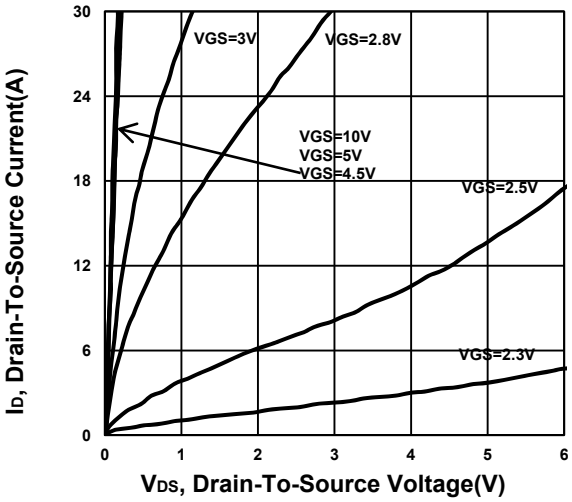
PARAMETER	SYMBOL	TEST CONDITIONS		LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	Q2	30			V
			Q1	30			
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	Q2	1.3	1.75	2.3	
			Q1	1.3	1.75	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	Q2			±100	nA
			Q1			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V	Q2			1	μA
			Q1			1	
		V_{DS} = 20V, V_{GS} = 0V, T_J = 55 °C	Q2			10	
			Q1			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} =4.5V, I_D = 10A	Q2		7	9.5	mΩ
		V_{GS} =4.5V, I_D = 6A	Q1		19.4	24	
		V_{GS} = 10V, I_D = 12A	Q2		5.4	7	
		V_{GS} = 10V, I_D = 7A	Q1		13	16	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 12A	Q2		55		S
		V_{DS} = 5V, I_D = 7A	Q1		34		
DYNAMIC							
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	Q2		941		pF
			Q1		331		
Output Capacitance	C_{oss}		Q2		172		
			Q1		71		
Reverse Transfer Capacitance	C_{rss}		Q2		118		
			Q1		48		
Total Gate Charge[2]	Q_g VGS = 10V	Q2 V_{DS} = 15V , V_{GS} = 10V, I_D = 12A Q1 V_{DS} = 15V , V_{GS} = 10V, I_D = 7A	Q2		21		nC
			Q1		8		
	Q_g VGS = 4.5V		Q2		14		
			Q1		4.4		
Gate-Source Charge[2]	Q_{gs}		Q2		2		
			Q1		1.2		
Gate-Drain Charge[2]	Q_{gd}		Q2		7		
			Q1		2.3		

Turn-On Delay Time[2]	$t_{d(on)}$	Q2 V_{DS} = 15V , $I_D \cong$ 12A, V_{GS} = 10V, R_{GEN} =6Ω Q1 V_{DS} = 15V , $I_D \cong$ 7A, V_{GS} = 10V, R_{GEN} =6Ω	Q2		28		nS
			Q1		17		
Rise Time[2]	t_r		Q2		23.8		
			Q1		17		
Turn-Off Delay Time[2]	$t_{d(off)}$		Q2		51		
			Q1		37		
Fall Time[2]	t_f		Q2		25		
			Q1		18		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)							
Continuous Current[3]	I_S		Q2			16	A
			Q1			11.4	
Forward Voltage[1]	V_{SD}	I_F = 12A, V_{GS} = 0V	Q2			1.2	V
		I_F = 7A, V_{GS} = 0V	Q1			1.4	
Reverse Recovery Time	t_{rr}	Q2 I_F = 12A, dI_F/dt = 100A / μS Q1 I_F = 7A, dI_F/dt = 100A / μS	Q2		16		nS
			Q1		8.8		
Reverse Recovery Charge	Q_{rr}		Q2		7		nC
			Q1		2.3		

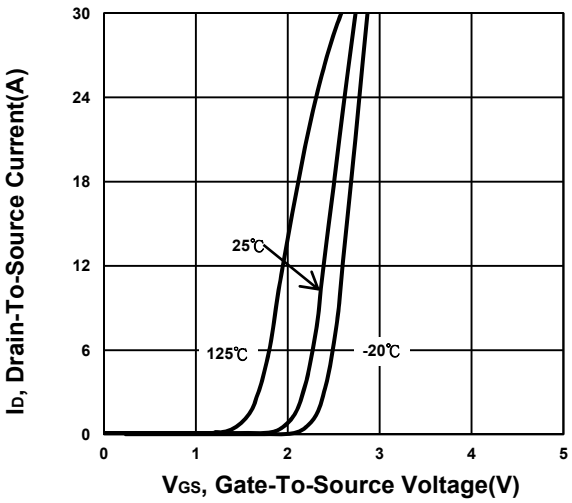
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.
[3]Package limitation current is Q2=19A , Q1=11A.

Q2 – Channel : Typical Characteristics

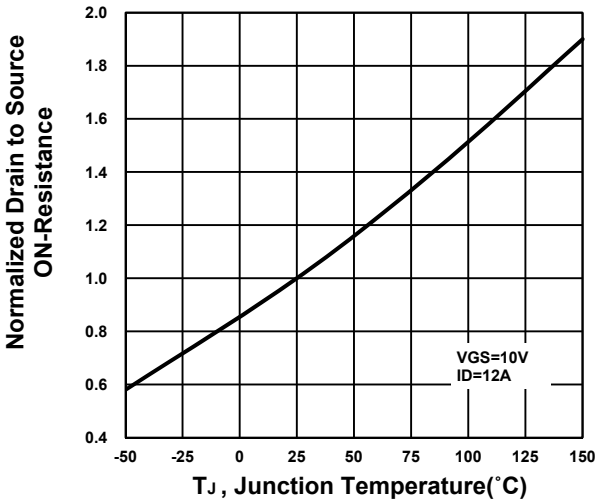
Output Characteristics



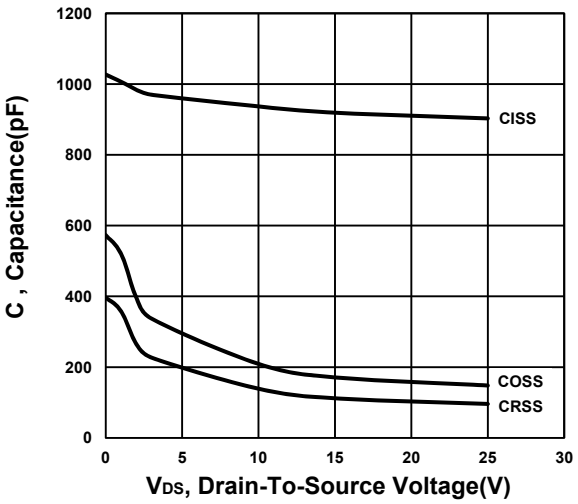
Transfer Characteristics



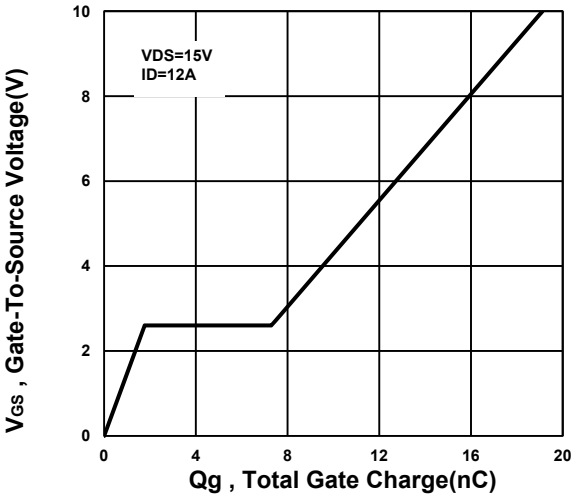
On-Resistance VS Temperature



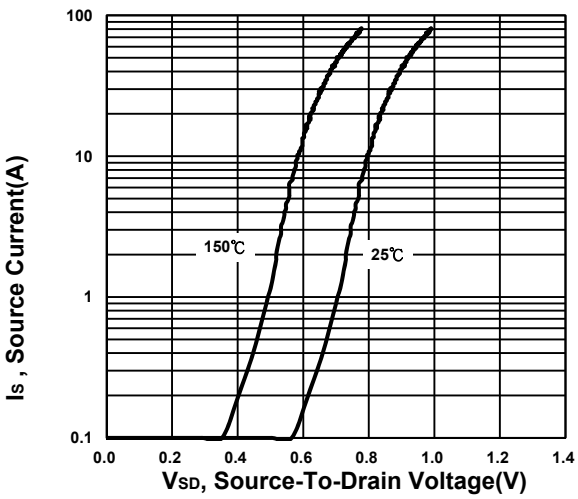
Capacitance Characteristic



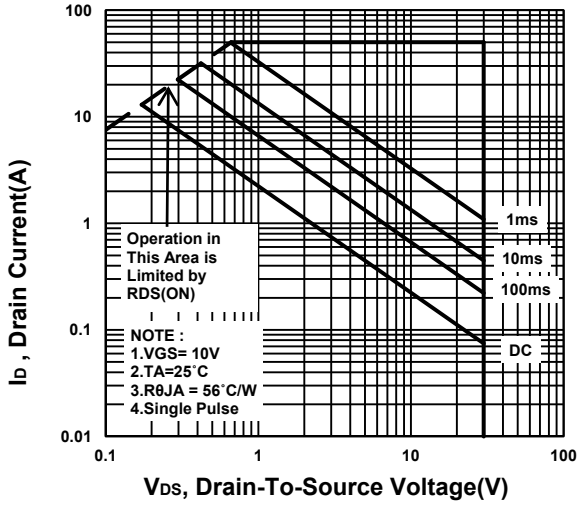
Gate charge Characteristics



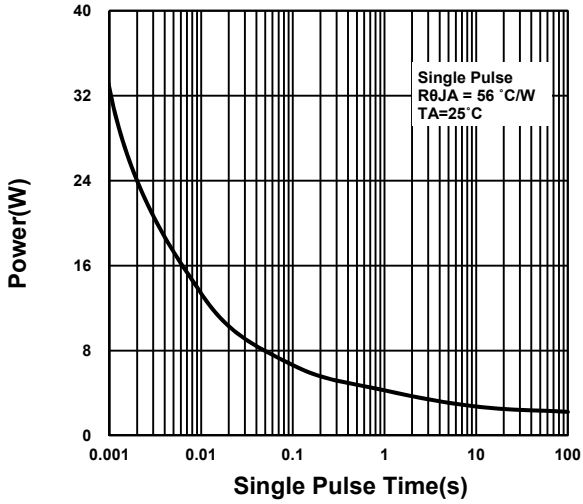
Source-Drain Diode Forward Voltage



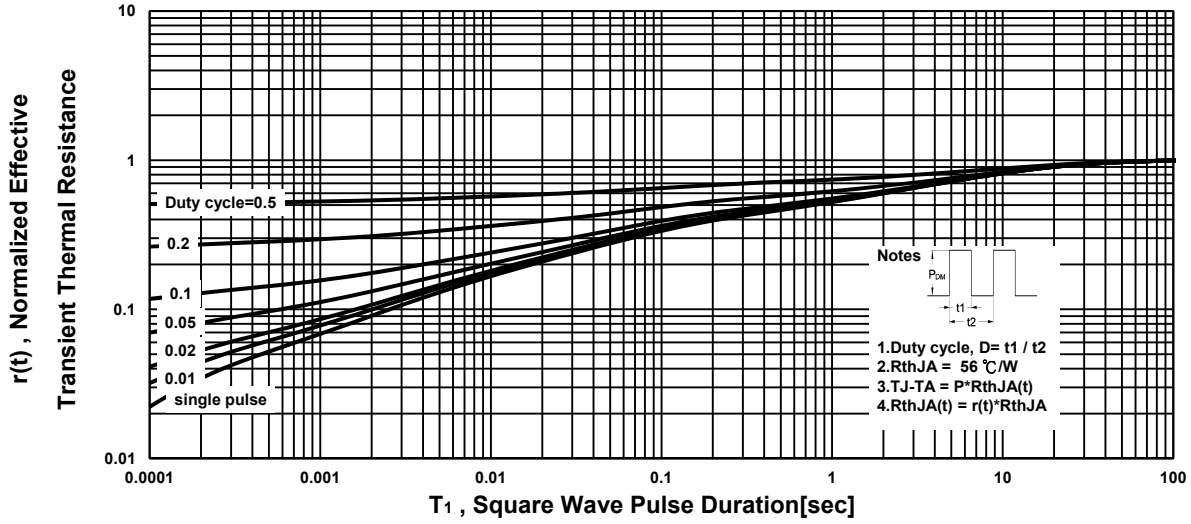
Safe Operating Area



Single Pulse Maximum Power Dissipation

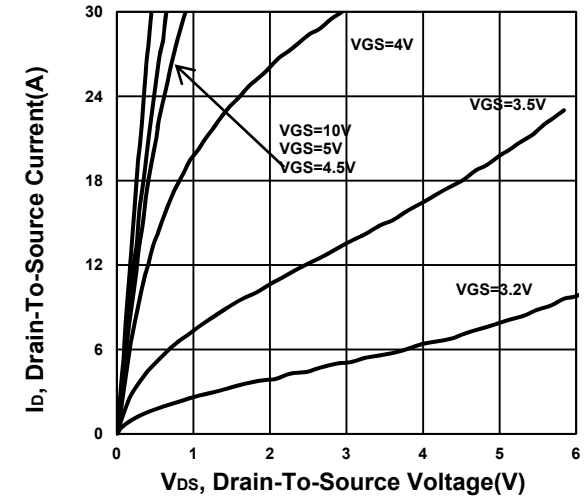


Transient Thermal Response Curve

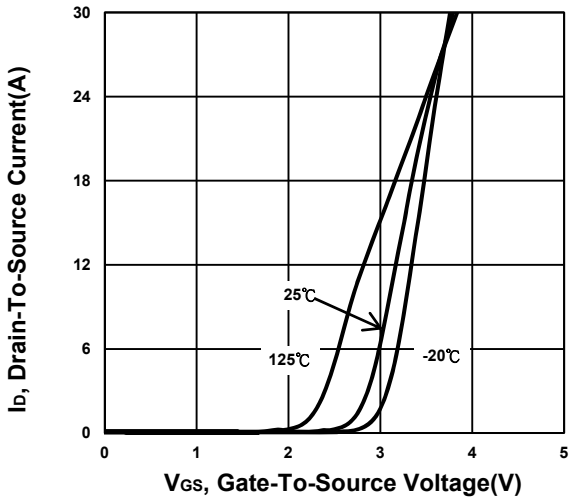


Q1 – Channel : Typical Characteristics

Output Characteristics



Transfer Characteristics



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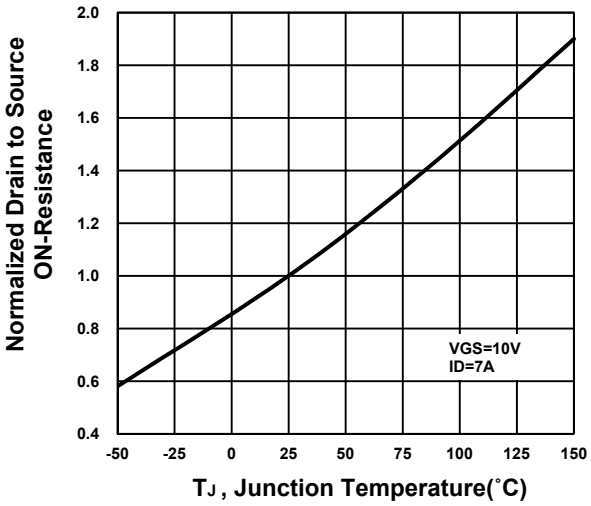

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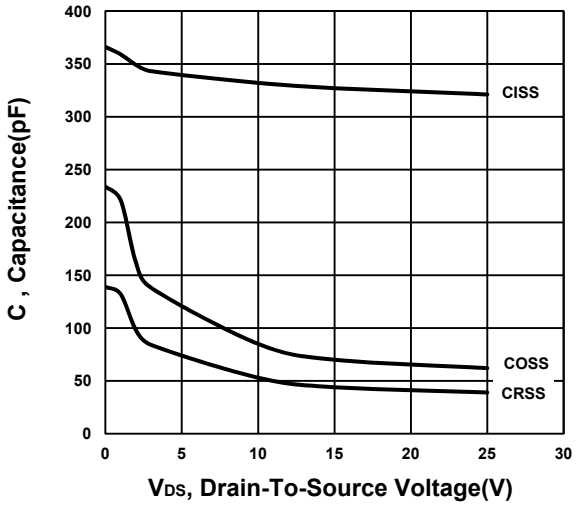
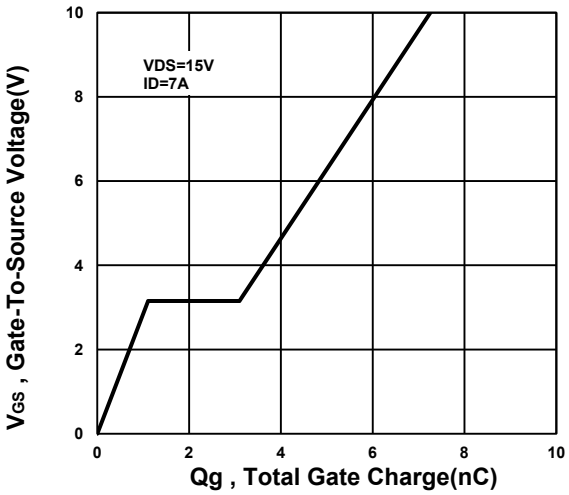


Gate charge Characteristics



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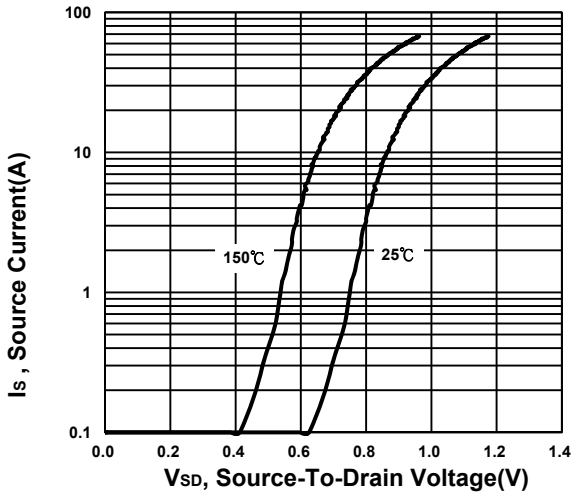

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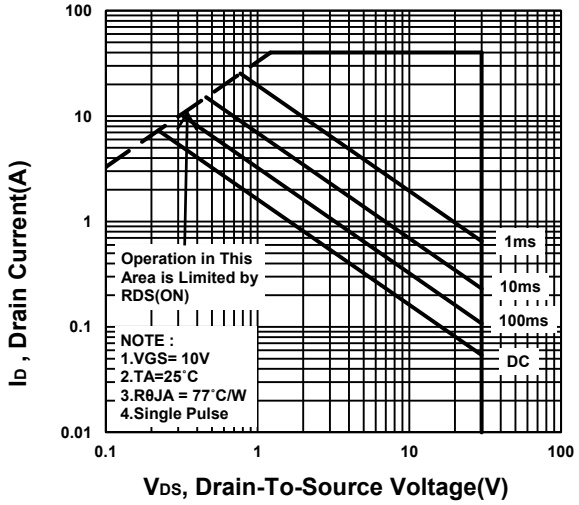

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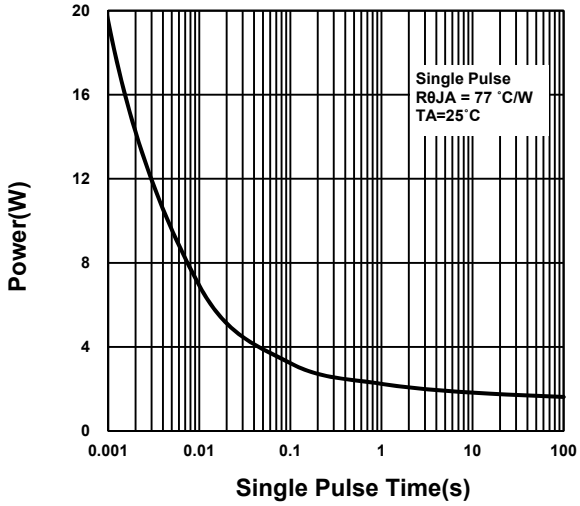

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